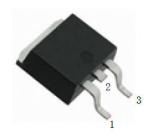
MJD117R-HAF

PNP Silicon Darlington Power Transistor

Features

 Halogen and Antimony Free(HAF), RoHS compliant



1.Base 2.Collector 3.Emitter TO-252 Plastic Package

Absolute Maximum Ratings (T_a = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	100	V
Collector Emitter Voltage	-V _{CEO}	100	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	2	Α
Peak Collector Current, Pulsed	-I _{CM}	4	Α
Base Current	-I _B	50	mA
Power Dissipation $T_a = 25^{\circ}\text{C}$ $T_c = 25^{\circ}\text{C}$	P _{tot}	1.75 20	W
Operating Junction Storage Temperature Range	T_{j},T_{stg}	- 65 to + 150	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{ heta JC}$	6.25	°C/W
Thermal Resistance from Junction to Ambient 1)	$R_{ hetaJA}$	71.4	°C/W

¹⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



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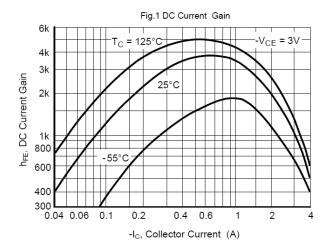
Characteristics at $T_a = 25^{\circ}C$ unless otherwise specified

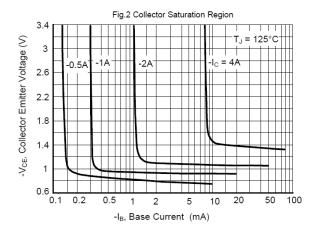
Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 3 \text{ V}$, $-I_{C} = 0.5 \text{ A}$ at $-V_{CE} = 3 \text{ V}$, $-I_{C} = 2 \text{ A}$ at $-V_{CE} = 3 \text{ V}$, $-I_{C} = 4 \text{ A}$	h _{FE} h _{FE} h _{FE}	500 1000 200	- 12000 -	- - -
Collector Emitter Cutoff Current at -V _{CE} = 50 V	-I _{CEO}	-	20	μΑ
Collector Base Cutoff Current at $-V_{CB}$ = 100 V at $-V_{CB}$ = 80 V	-I _{CBO}		20 10	μΑ
Emitter Base Cutoff Current at -V _{EB} = 5 V	-I _{EBO}	-	2	mA
Collector Base Breakdown Voltage at -I _C = 100 µA	-V _{(BR)CBO}	100		
Collector Emitter Breakdown Voltage at -I _C = 1 mA	-V _{(BR)CEO}	100		
Emitter Base Breakdown Voltage at -I _E = 100 µA	-V _{(BR)EBO}	5		
Collector Emitter Saturation Voltage at $-I_C = 2 \text{ A}$, $-I_B = 8 \text{ mA}$ at $-I_C = 4 \text{ A}$, $-I_B = 40 \text{ mA}$	-V _{CE(sat)}	-	2 3	V
Base Emitter Saturation Voltage at $-I_C = 4 \text{ A}$, $-I_B = 40 \text{ mA}$	-V _{BE(sat)}	-	4	V
Base Emitter Voltage at -V _{CE} = 3 V, -I _C = 2 A	-V _{BE(on)}	-	2.8	V
Current Gain Bandwidth Product at $-V_{CE} = 10 \text{ V}$, $-I_{C} = 750 \text{ mA}$, $f = 1 \text{ MHz}$	f _T	25	-	MHz
Output Capacitance at -V _{CB} = 10 V, f = 0.1 MHz	C _{ob}	-	200	pF

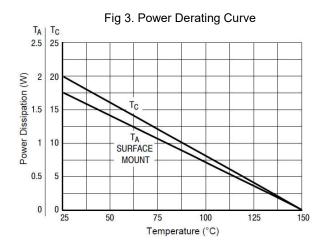


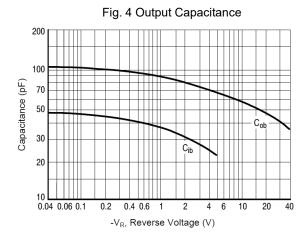
MJD117R-HAF

Electrical Characteristics Curves



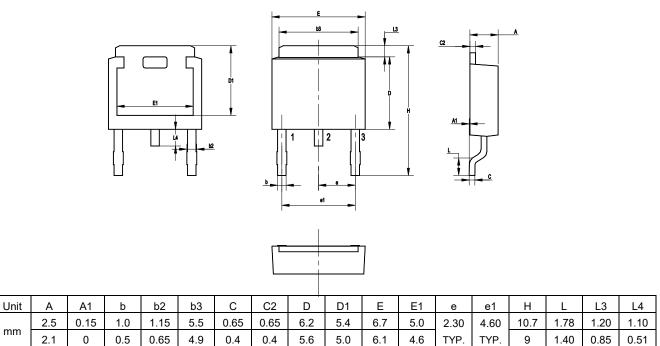




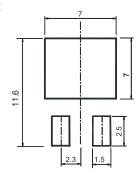


Package Outline Dimensions (Units: mm)

TO-252



Recommended Soldering Footprint



Packing information

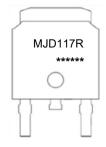
Tape Width		Pi	tch	Reel Size		Par Pool Pooking Quantity
Package	(mm)	mm	inch	mm	inch	Per Reel Packing Quantity
TO-252	16	8 ± 0.1	0.315 ± 0.004	330	13	2,500

Marking information

" MJD117R " = Part No.

" ***** " = Date Code Marking

Font type: Arial



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